

IN THE ABSTRACT

Please add the following Abstract of the Disclosure on a new page after the claims of this application:

--SEMICONDUCTING DEVICES AND METHOD OF MAKING THEREOF

ABSTRACT OF THE DISCLOSURE

The invention relates to a process for providing a semiconducting device including the steps of depositing a semiconducting layer onto a substrate by means of heating a gas to a predetermined, disassociation temperature so that the gas dissociates into fractions, whereby these fractions subsequently condense on the substrate to build up a semiconducting layer.--

REMARKS

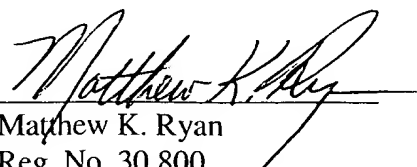
Please enter this Supplemental Preliminary Amendment in the file of this application. By this Supplemental Preliminary Amendment, an Abstract of the Disclosure has been added for this application and a copy of the Declaration and Power of Attorney as filed in the parent application (Serial No. 09/331,528) is attached.

Attached hereto is a marked-up version of the changes made to the application by the current amendment. The attached page is captioned **"Version with markings to show changes made."**

Please charge any additional fees incurred by reason of this response and not paid herewith to Deposit Account No. 50-0320.

Respectfully submitted,
FROMMER LAWRENCE & HAUG LLP
Attorneys for Applicants

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"VERSION WITH MARKINGS TO SHOW CHANGES MADE."

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